

TO-220-3L Plastic-Encapsulate Transistors

KTB1366 TRANSISTOR (PNP)

FEATURES

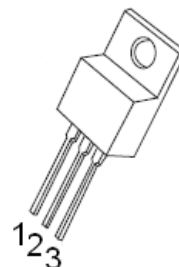
- Low Collector Saturation Voltage
- Complementary to KTD2058

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current	-3	A
P_C	Collector Power Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	63	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

TO-220-3L

1. BASE
2. COLLECTOR
3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-7\text{V}, I_C=0$			-100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$	60		200	
	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-3\text{A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$			-1	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		150		pF
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$		9		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y
RANGE	60-120	100-200